

1. General description

WeEnPACK-B1 module with WeEn 1200V Gen2 SiC MOSFET and Solder pin type. Integrated with NTC temperature sensor.



2. Features and benefits

- H Bridge topology
- Solder pin type
- Low $R_{DS(on)}$
- Low Switching Losses
- Low Q_g and C_{rss}
- Low Inductive Design

3. Applications

- Power inverters
- AC-DC converters
- Active power factor correctors
- Motor drives

4. Quick reference data

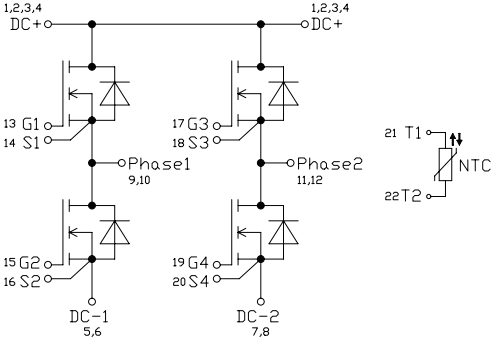
Table 1. Quick reference data

Table 17: Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V _{DS}	drain-source voltage	T _j = 25 °C		1200			V
I _D	drain current	V _{GS} = 18 V; T _h = 25 °C		38			A
P _{tot}	total power dissipation	T _h = 25 °C		74			W
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 15 V; I _D = 33 A; T _j = 25 °C		-	40	-	mΩ
		V _{GS} = 18 V; I _D = 33 A; T _j = 25 °C		-	33	45	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 33 A; V _{DS} = 800 V; V _{GS} = -4 V/18 V; T _j = 25 °C		-	115	-	nC
Q _{GD}	gate-drain charge			-	18	-	nC
Source-drain diode							
Q _r	recovered charge	I _{SD} = 33 A; V _{GS} = -4 V/18 V; V _R = 600 V; di/dt = 3400 A/μs; R _{G(ext)} = 5.1 Ω; T _j = 25 °C		-	465	-	nC

5. Pinning information

Table 2. Pinning information

Simplified outline	Circuit diagram
 * Please refer to the package outline description for actual pin order.	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMSC040F12B1S	WeEnPACK-B1	WMSC040F12B1S6T	Tray	24	WeEnPACK-B1PFB-E	01-Sep-2025

7. Marking

Table 4. Marking codes

Type number	Marking codes
WMSC040F12B1S	WMSC040F12B1S

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
T _{stg}	storage temperature			-40 to 125	°C
T _{j,op}	operating junction temperature			-40 to 150	°C
T _{j,max}	maximum junction temperature	Intermittent condition with shortened lifetime		-40 to 175	°C
V _{ISOL}	RMS isolation voltage	T _j = 25 °C; all terminals shorted; f = 50 Hz; t = 1 s		3500	V
MOSFET					
V _{DS}	drain-source voltage	T _j = 25 °C		1200	V
V _{GS,max}	gate-source voltage	Absolute maximum values		-12 to 24	V
V _{GS,op}	gate-source voltage	Recommended operational values		-4 to 18	V
P _{tot}	total power dissipation	T _h = 25 °C		74	W
I _D	drain current	V _{GS} = 18 V; T _h = 25 °C		38	A
		V _{GS} = 18 V; T _h = 100 °C		24	A
I _{DM}	peak drain current	pulse width tp limited by T _{j,max}		80	A
E _{as}	single pulse drain-to-source avalanche	I _{AS} = 24 A; L = 1 mH; V _{DD} = 100 V; T _{j(init)} = 25 °C; per MOSFET		288	mJ
Body Diode					
I _{SD}	DC body diode forward current	T _h = 25 °C; V _{GS} = -4 V		18	A
I _{SD,pulse}	Pulse body diode current	verified by design, tp limited by T _{j,max}		80	A

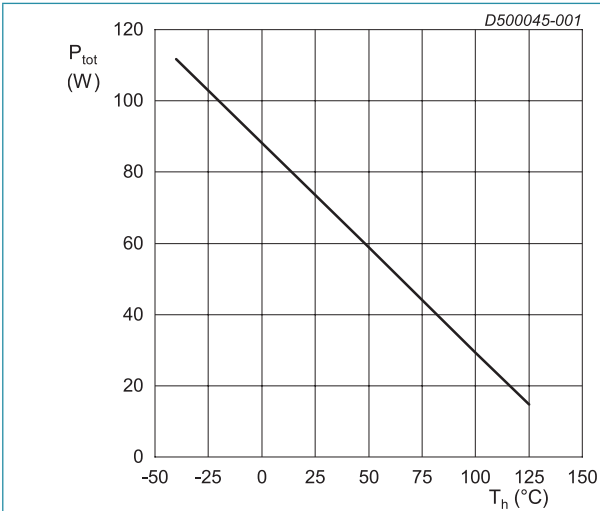


Fig. 1. Power dissipation as a function of heatsink temperature; maximum values

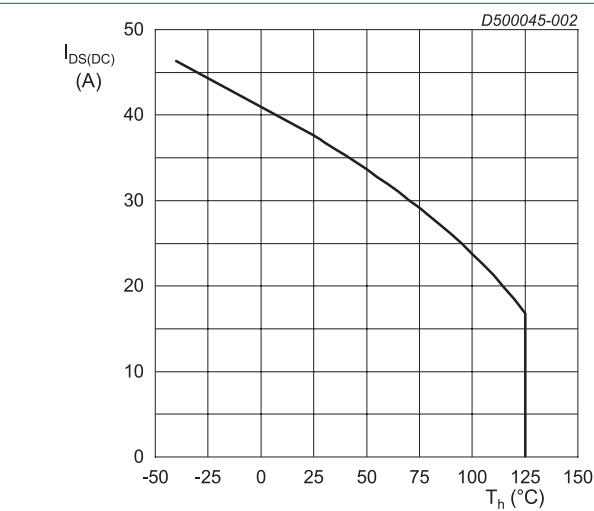


Fig. 2. Continuous Drain Current as a function of heatsink temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	per MOSFET		-	0.75	-	K/W
$R_{th(j-h)}$	thermal resistance from junction to heatsink	per MOSFET, $\lambda_{grease} = 3 \text{ W/(m}\cdot\text{K)}$ $thick_{grease} = 50 \text{ }\mu\text{m}$		-	1.7	-	K/W
Internal Isolation		basic insulation (class 1, IEC 61140)		Al_2O_3			
d_{Creep}	Creepage distance	terminal to heatsink		-	11.5	-	mm
		terminal to terminal		-	6.3	-	mm
d_{Clear}	Clearance	terminal to heatsink		-	10	-	mm
		terminal to terminal		-	5	-	mm
CTI	Comperative tracking index			>200			
F	Mounting force per clamp			20	-	50	N
G	Approximate Weight			-	20	-	g

Note: Module is ESD sensitive. Handling precautions are recommanded.

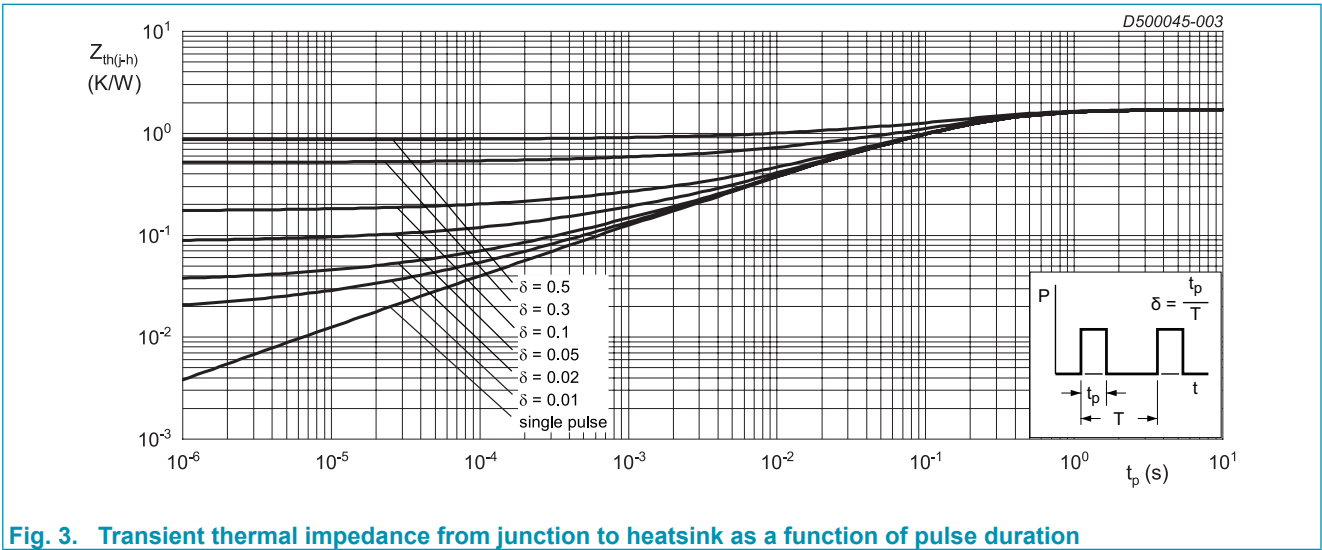


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Characteristics

Table 7. Characteristics

MOSFET							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100 \mu A$; $V_{GS} = 0 V$; $T_j = 25^\circ C$		1200	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 10 mA$; $V_{DS} = V_{GS}$; $T_j = 25^\circ C$		1.9	2.6	3.5	V
		$I_D = 10 mA$; $V_{DS} = V_{GS}$; $T_j = 175^\circ C$		-	1.9	-	V
I_{DSS}	drain leakage current	$V_{DS} = 1200 V$; $V_{GS} = 0 V$; $T_j = 25^\circ C$		-	0.2	100	μA
I_{GSS}	gate leakage current (absolute value)	$V_{GS} = 24 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$		-	10	100	nA
		$V_{GS} = -12 V$; $V_{DS} = 0 V$; $T_j = 25^\circ C$		-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15 V$; $I_D = 33 A$; $T_j = 25^\circ C$		-	40	-	m Ω
		$V_{GS} = 18 V$; $I_D = 33 A$; $T_j = 25^\circ C$		-	33	45	m Ω
		$V_{GS} = 18 V$; $I_D = 33 A$; $T_j = 125^\circ C$		-	46	-	m Ω
		$V_{GS} = 18 V$; $I_D = 33 A$; $T_j = 150^\circ C$		-	51	-	m Ω
		$V_{GS} = 18 V$; $I_D = 33 A$; $T_j = 175^\circ C$		-	54	-	m Ω
R_G	gate resistance	$f = 1 MHz$; $T_j = 25^\circ C$; per MOSFET		-	1	-	Ω
g_{fs}	transconductance	$V_{DS} = 20 V$; $I_D = 33 A$; $T_j = 25^\circ C$		-	20	-	S
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 33 A$; $V_{DS} = 800 V$; $V_{GS} = -4 V/18 V$; $T_j = 25^\circ C$		-	115	-	nC
Q_{GS}	gate-source charge			-	47	-	nC
Q_{GD}	gate-drain charge			-	18	-	nC
C_{iss}	input capacitance	$V_{DS} = 1000 V$; $V_{GS} = 0 V$; $f = 100 KHz$; $T_j = 25^\circ C$		-	2.45	-	nF
C_{oss}	output capacitance			-	108	-	pF
C_{rss}	reverse transfer capacitance			-	11	-	pF
E_{oss}	Coss stored energy			-	54	-	μJ
$t_{d(on)}$	turn-on delay time	$V_{DS} = 800 V$; $V_{GS} = -4 V/18 V$; $R_{G(ext)} = 5.1 \Omega$; $I_D = 33 A$; $L = 300 \mu H$; $T_j = 25^\circ C$		-	27	-	ns
t_r	rise time			-	30	-	ns
$t_{d(off)}$	turn-off delay time			-	42	-	ns
t_f	fall time			-	11	-	ns
E_{on}	turn-on energy			-	612	-	μJ
E_{off}	turn-off energy			-	90	-	μJ

Body diode							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V _{SD}	source-drain voltage	V _{GS} = -4 V; I _{SD} = 33 A; T _j = 25 °C		-	5.5	-	V
		V _{GS} = -4 V; I _{SD} = 33 A; T _j = 150 °C		-	5.0	-	V
Dynamic characteristics							
I _{rrm}	reverse recovery current	I _{SD} = 33 A; V _{GS} = -4 V/18 V; V _R = 600 V; di/dt = 3400 A/μs; R _{G(ext)} = 5.1 Ω; T _j = 25 °C		-	44	-	A
t _{rr}	reverse recovery time			-	19	-	ns
Q _r	recovered charge			-	465	-	nC
E _{rec}	reverse recovery energy			-	117	-	μJ
NTC thermistor							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
R ₂₅	Rated resistance	T _{NTC} = 25 °C		-	5000	-	Ω
R ₁₀₀		T _{NTC} = 100 °C		465±5%			Ω
B _{25/50}	B-value	R ₂ = R ₂₅ exp[B _{25/50} (1/T ₂ - 1/(298.15K))]		3380			K
	Maximum operating temperature			-	200	-	°C
	Dissipation costant			-	2	-	mW/K
	Thermal time constant			-	≤10	-	s

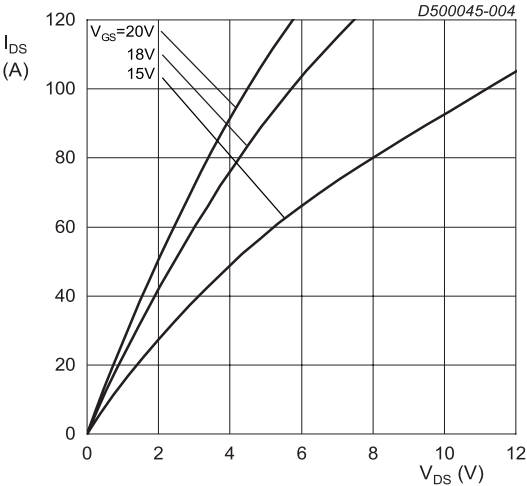


Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values

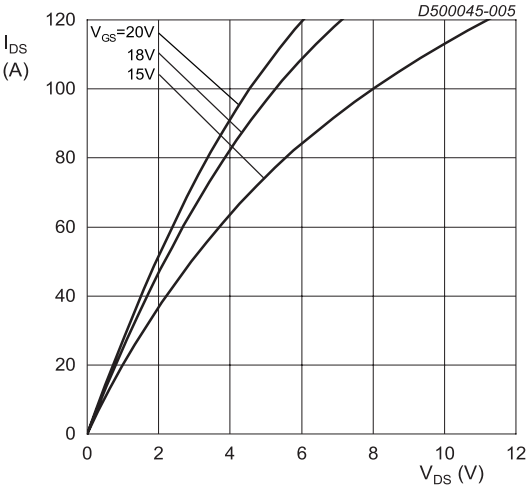


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

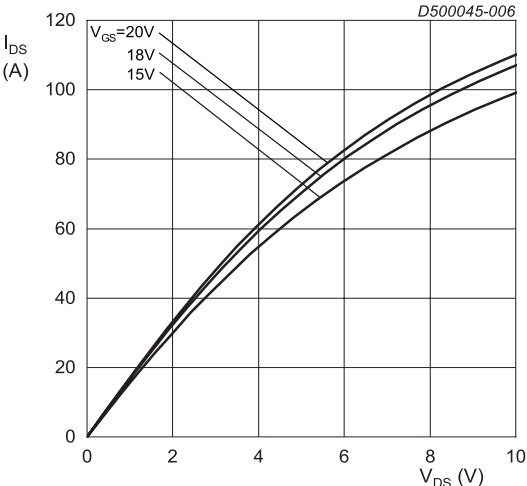


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

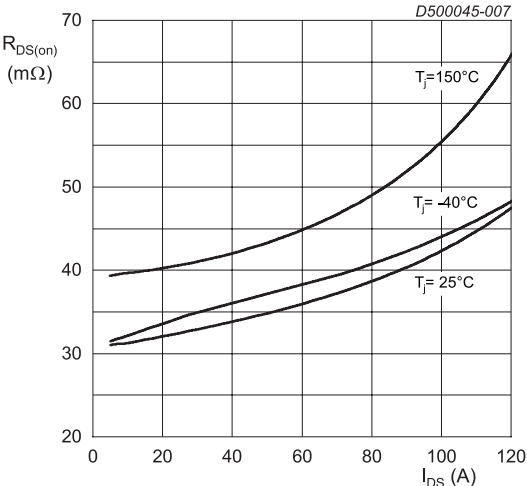
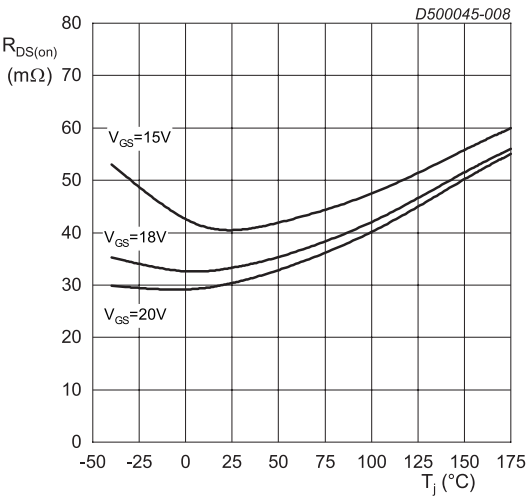
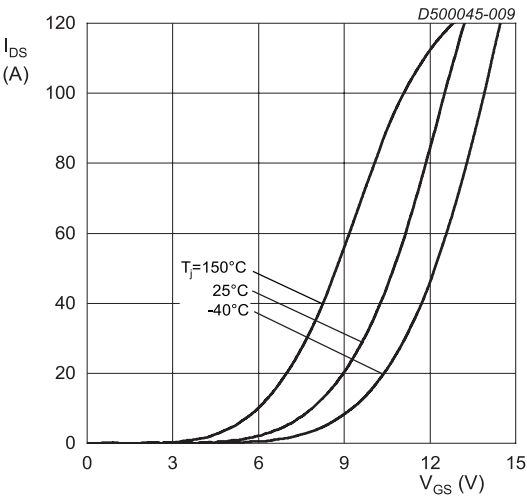


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



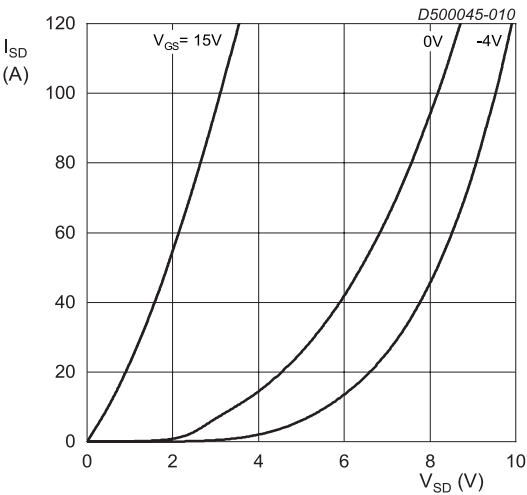
$I_{DS} = 33\text{ A}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 8. Drain-source on-state resistance as a function of junction temperature



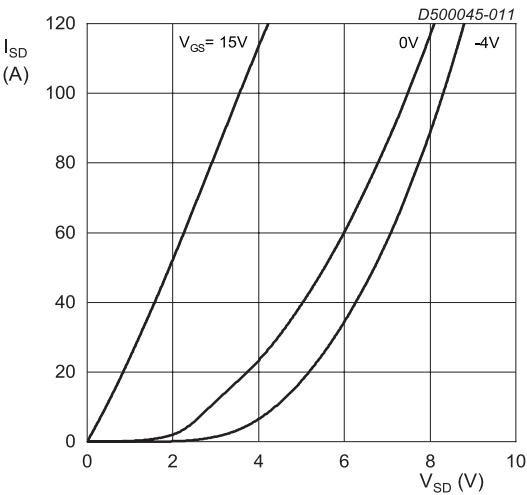
$V_{DS} = 20\text{ V}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



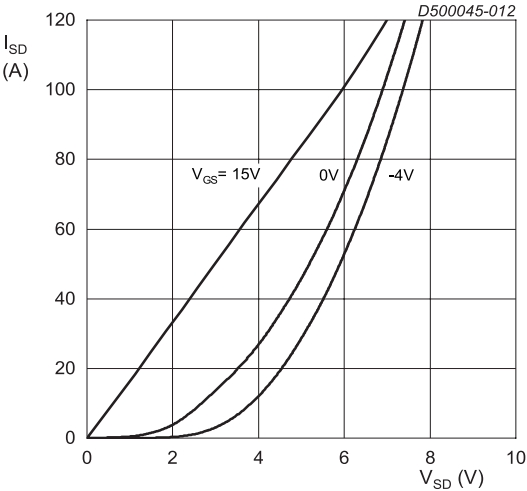
$T_j = -40\text{ }^\circ\text{C}$; $t_p < 200\text{ }\mu\text{s}$

Fig. 10. Body diode forward characteristics; typical values

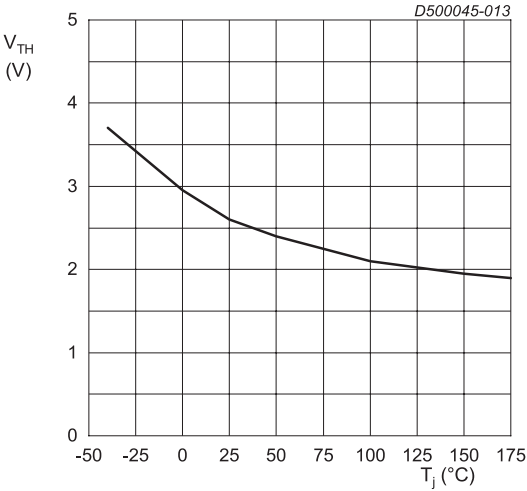


$T_j = 25\text{ }^\circ\text{C}$; $t_p < 200\text{ }\mu\text{s}$

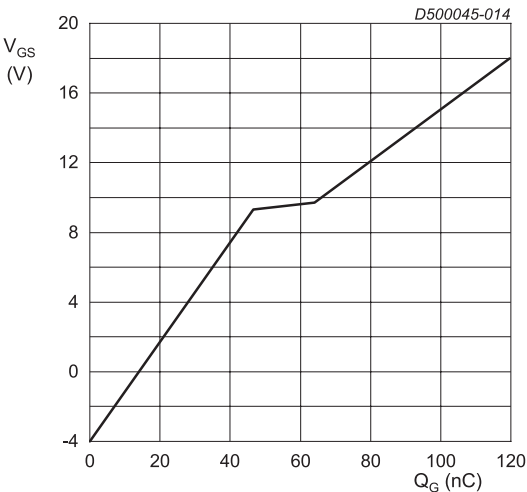
Fig. 11. Body diode forward characteristics; typical values



$T_j = 150\text{ }^{\circ}\text{C}$; $t_p < 200\text{ }\mu\text{s}$
Fig. 12. Body diode forward characteristics; typical values



$V_{DS} = 10\text{ V}$; $I_{DS} = 10\text{ mA}$
Fig. 13. Threshold voltage as a function of junction temperature



$I_{DS} = 33\text{ A}$; $I_{GS} = 0.1\text{ mA}$; $V_{DS} = 800\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$
Fig. 14. Gate-source voltage as a function of gate charge; typical values

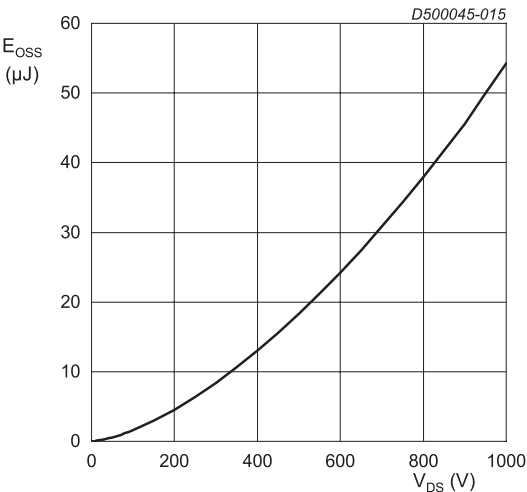
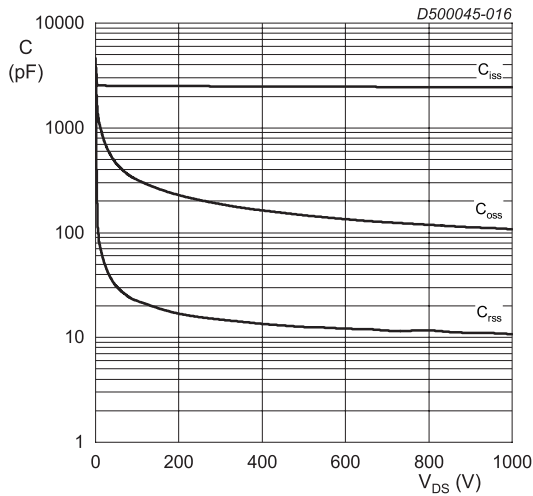
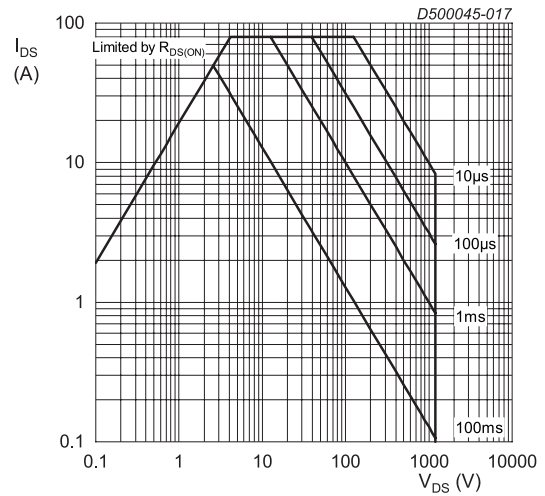


Fig. 15. Output capacitor stored energy as a function of drain-source voltage



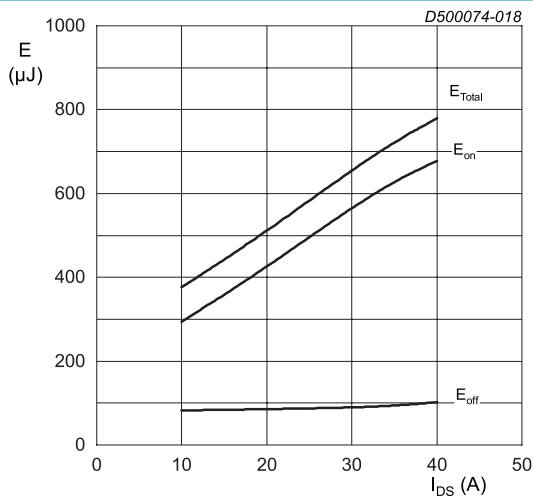
$V_{DS} = 0 - 1000$ V
 $T_j = 25$ °C; $V_{AC} = 25$ mV; $f = 100$ KHz

Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



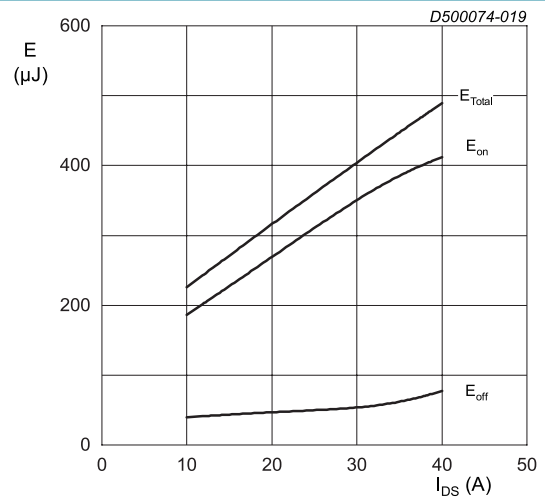
$T_j = 25$ °C; $D = 0$
 Parameter: t_p

Fig. 17. Forward bias safe operating area



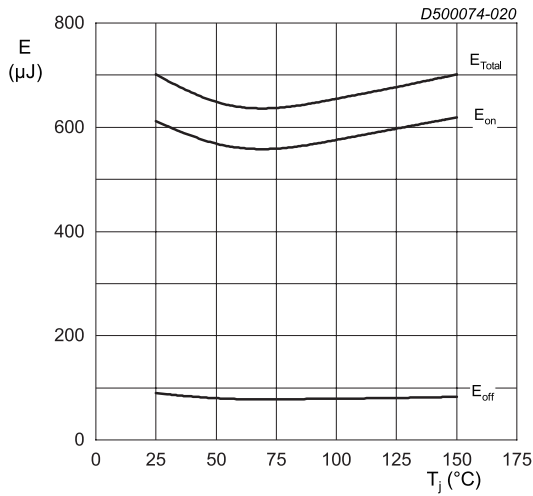
$T_j = 25$ °C; $V_{DD} = 800$ V; $R_{G(ext)} = 5.1$ Ω; $R_{G(on)} = 5.1$ Ω;
 $V_{GS} = -4$ V/18 V; $L = 300$ μH

Fig. 18. Clamped Inductive Switching Energy as a function of drain current



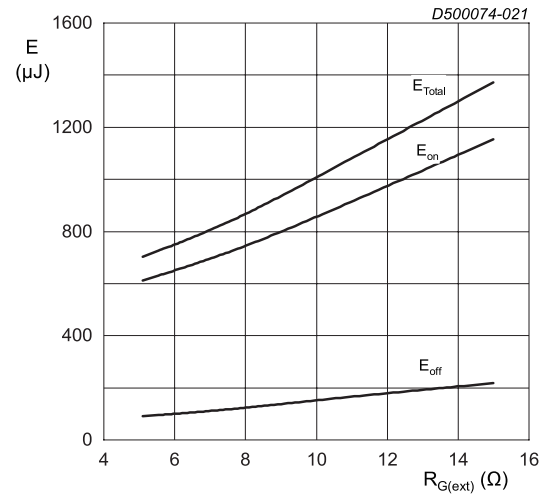
$T_j = 25$ °C; $V_{DD} = 600$ V; $R_{G(off)} = 5.1$ Ω; $R_{G(on)} = 5.1$ Ω;
 $V_{GS} = -4$ V/18 V; $L = 300$ μH

Fig. 19. Clamped Inductive Switching Energy as a function of drain current



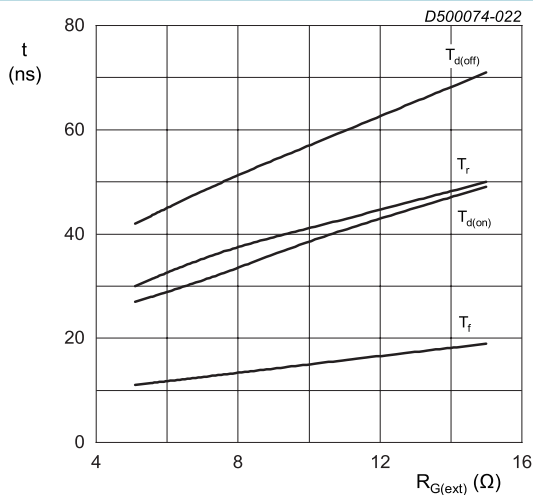
$I_{DS} = 33\text{ A}$; $V_{DD} = 800\text{ V}$; $R_{G(off)} = 5.1\ \Omega$; $R_{G(on)} = 5.1\ \Omega$;
 $V_{GS} = -4\text{ V}/18\text{ V}$; $L = 300\ \mu\text{H}$

Fig. 20. Clamped Inductive Switching Energy as a function of junction temperature



$T_j = 25\text{ °C}$; $V_{DD} = 800\text{ V}$; $I_{DS} = 33\text{ A}$; $V_{GS} = -4\text{ V}/18\text{ V}$;
 $L = 300\ \mu\text{H}$

Fig. 21. Clamped Inductive Switching Energy as a function of external gate resistance



$T_j = 25\text{ °C}$; $V_{DD} = 800\text{ V}$; $I_{DS} = 33\text{ A}$; $V_{GS} = -4\text{ V}/18\text{ V}$;
 $L = 300\ \mu\text{H}$

Fig. 22. Switching time as a function of external gate resistance

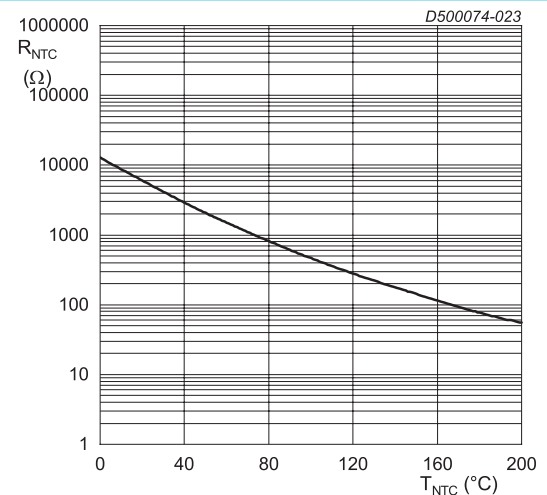
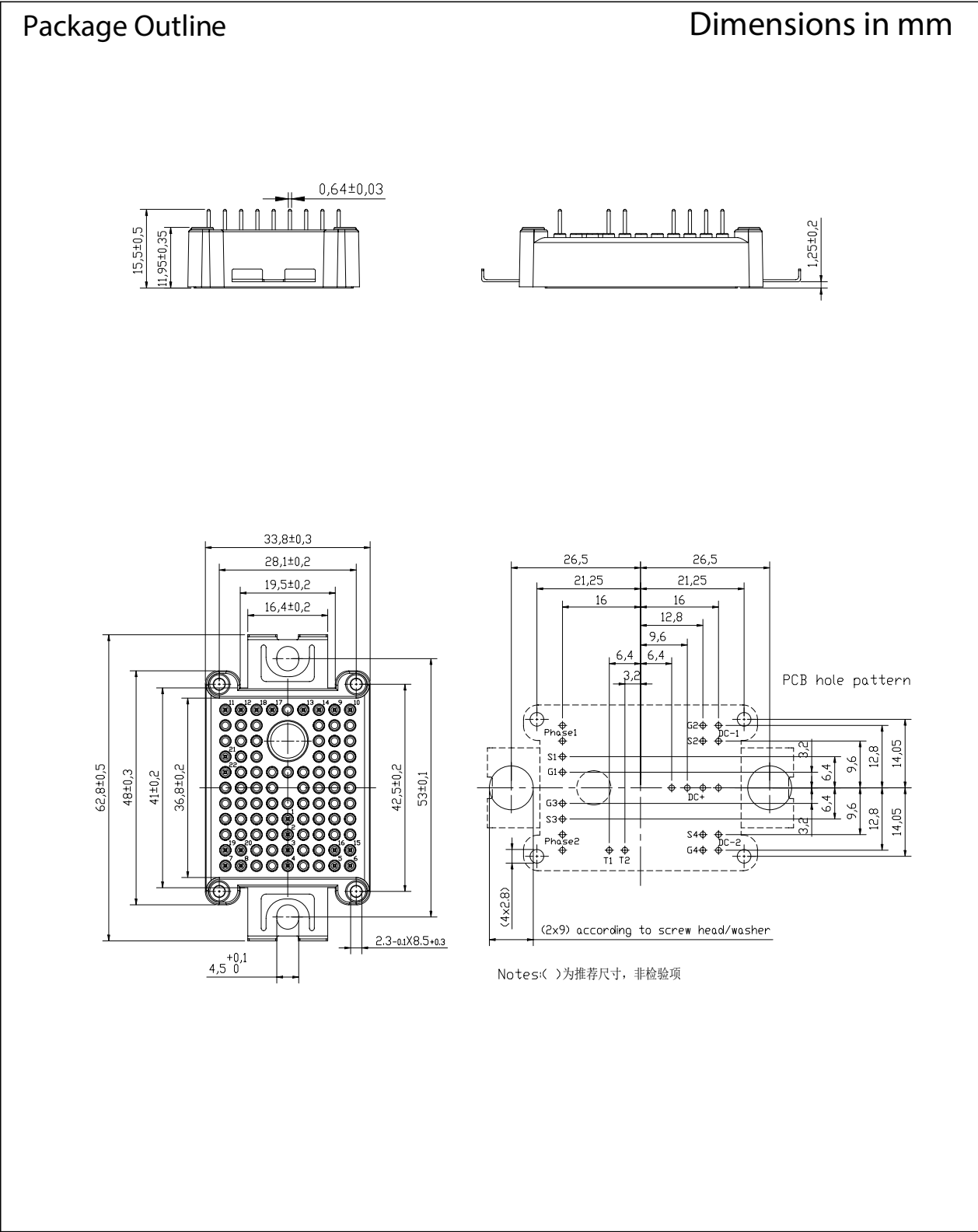


Fig. 23. NTC thermistor resistance as a function of NTC temperature

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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For sales office addresses, please send an email to: salesaddresses@ween-semi.com

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